

U.S. Application No.: 09/768,912

Atty. Docket No. 09792909.4785

**AMENDMENTS TO THE CLAIMS:**

1.-8. (Previously Cancelled)

9. (Currently Amended) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, and

a device formed on one major surface of said single-crystal substrate by using III-V compound semiconductors,

a layer disposed on said major surface of said single-crystal substrate and in electrical connection with said device; and

~~wherein electrical connection to said device is made through~~

~~a via hole formed in said single-crystal substrate through to said layer;~~

wherein an electrical connection to said device is created through said via hole and contact with said layer.

10. (Previously Presented) The semiconductor device according to claim 9, wherein said single-crystal substrate is one of a sapphire substrate, spinel substrate, perovskite yttrium aluminate substrate and SiC substrate.

11. (Original) The semiconductor device according to claim 9 wherein said semiconductor device is a semiconductor laser using nitride III-V compound semiconductors.

12. (Previously Presented) The semiconductor device according to claim 9 wherein said semiconductor device is an FET using nitride III-V compound semiconductors.

13.-24. (Canceled)